

CD4002M/CD4002C Dual 4-Input NOR Gate CD4012M/CD4012C Dual 4-Input NAND Gate

General Description

These NOR and NAND gates are monolithic complementary MOS (CMOS) integrated circuits. The N- and P-channel enhancement mode transistors provide a symmetrical circuit with output swings essentially equal to the supply voltage. This results in high noise immunity over a wide supply voltage range. No DC power other than that caused by leakage current is consumed during static conditions. All inputs are protected against static discharge and latching conditions.

Features

- Wide supply voltage range
- Low power
- High noise immunity

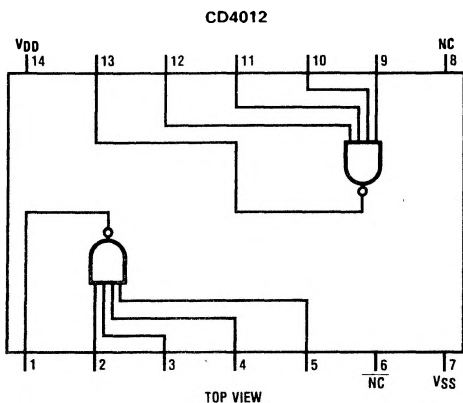
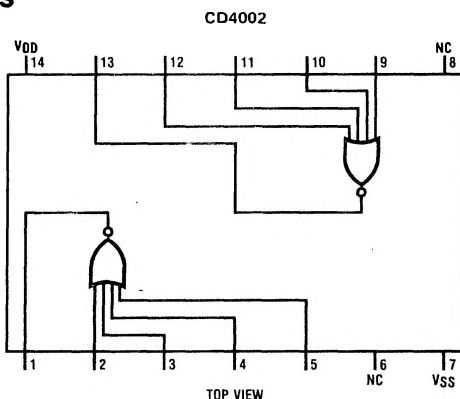
3.0V to 15V
10nW (typ.)
0.45V_{DD} (typ.)

Applications

- Automotive
- Data terminals
- Instrumentation
- Medical Electronics

- Alarm system
- Industrial controls
- Remote metering
- Computers

Connection Diagrams



Absolute Maximum Ratings (Note 1)

Voltage an Any Pin $V_{SS} - 0.3V$ to $V_{DD} + 0.3V$
 Operating Temperature Range
 CD4002M, CD4012M -55°C to $+125^{\circ}\text{C}$
 CD4002C, CD4012C -40°C to $+85^{\circ}\text{C}$

Storage Temperature Range -65°C to $+150^{\circ}\text{C}$
 Package Dissipation 500 mW
 Operating V_{DD} Range $V_{SS} + 3.0V$ to $V_{SS} + 15V$
 Lead Temperature (Soldering, 10 seconds) 300°C

DC Electrical Characteristics — CD4002M, CD4012M

Parameter		Conditions	Limits						Units	
			-55°C		25°C			125°C		
			Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Device Current	V _{DD} = 5.0V		0.05		0.001	0.05		3.0	μA
		V _{DD} = 10V		0.1		0.001	0.1		6.0	μA
P _D	Quiescent Device Dissipation/Package	V _{DD} = 5.0V		0.25		0.005	0.25		15	μW
		V _{DD} = 10V		1.0		0.01	1.0		60	μW
V _{OL}	Output Voltage Low Level	V _{DD} = 5.0V, V _I = V _{DD} , I _O = 0A		0.05		0	0.05		0.05	V
		V _{DD} = 10V, V _I = V _{DD} , I _O = 0A		0.05		0	0.05		0.05	V
V _{OH}	Output Voltage High Level	V _{DD} = 5.0V, V _I = V _{SS} , I _O = 0A	4.95		4.95	5.0		4.95		V
		V _{DD} = 10V, V _I = V _{SS} , I _O = 0A	9.95		9.95	10		9.95		V
V _{NL}	Noise Immunity (All Inputs)	V _{DD} = 5.0V, V _O = 3.6V, I _O = 0A	1.5		1.5	2.25		1.4		V
		V _{DD} = 10V, V _O = 7.2V, I _O = 0A	3.0		3.0	4.5		2.9		V
V _{NH}	Noise Immunity (All Inputs)	V _{DD} = 5.0V, V _O = 0.95V, I _O = 0A	1.4		1.5	2.25		1.5		V
		V _{DD} = 10V, V _O = 2.9V, I _O = 0A	2.9		3.0	4.5		3.0		V
I _{DN}	Output Drive Current N-Channel (4002)	V _{DD} = 5.0V, V _O = 0.4V, V _I = V _{DD}	0.5		0.40	1.0		0.28		mA
		V _{DD} = 10V, V _O = 0.5V, V _I = V _{DD}	1.1		0.9	2.5		0.65		mA
I _{DP}	Output Drive Current P-Channel (4002)	V _{DD} = 5.0V, V _O = 2.5V, V _I = V _{SS}	-0.62		-0.5	-2.0		-0.35		mA
		V _{DD} = 10V, V _O = 9.5V, V _I = V _{SS}	-0.62		-0.5	-1.0		-0.35		mA
I _{DN}	Output Drive Current N-Channel (4012)	V _{DD} = 5.0V, V _O = 0.4V, V _I = V _{DD}	0.31		0.25	0.5		0.175		mA
		V _{DD} = 10V, V _O = 0.5V, V _I = V _{DD}	0.63		0.5	0.6		0.35		mA
I _{DP}	Output Drive Current P-Channel (4012)	V _{DD} = 5.0V, V _O = 2.5V, V _I = V _{SS}	-0.31		-0.25	-0.5		-0.175		mA
		V _{DD} = 10V, V _O = 9.5V, V _I = V _{SS}	-0.75		-0.6	-1.2		-0.4		mA
I _I	Input Current					10				pA

DC Electrical Characteristics — CD4002C, CD4012C

Parameter		Conditions	Limits						Units	
			-40°C		25°C			85°C		
			Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Device Current	V _{DD} = 5.0V V _{DD} = 10V		0.5 5.0		0.005 0.005	0.5 5.0		15 30	μA
P _D	Quiescent Device Dissipation/Package	V _{DD} = 5.0V V _{DD} = 10V		2.5 50		0.025 0.05	2.5 50		75 300	μW
V _{OL}	Output Voltage Low Level	V _{DD} = 5.0V, V _I = V _{DD} , I _O = 0A V _{DD} = 10V, V _I = V _{DD} , I _O = 0A		0.05 0.05		0 0	0.05 0.05		0.05 0.05	V
V _{OH}	Output Voltage High Level	V _{DD} = 5.0V, V _I = V _{SS} , I _O = 0A V _{DD} = 10V, V _I = V _{SS} , I _O = 0A	4.95 9.95		4.95 9.95	5.0 10		4.95 9.95		V
V _{NL}	Noise Immunity (All Inputs)	V _{DD} = 5.0V, V _O ≥ 3.5V, I _O = 0A V _{DD} = 10V, V _O ≥ 7.2V, I _O = 0A	1.5 3.0		1.5 3.0	2.25 4.5		1.4 2.9		V
V _{NH}	Noise Immunity (All Inputs)	V _{DD} = 5.0V, V _O ≤ 1.5V, I _O = 0A V _{DD} = 10V, V _O ≤ 3.5V, I _O = 0A	1.4 2.9		1.5 3.0	2.25 4.5		1.5 3.0		V
I _{DN}	Output Drive Current N-Channel (4002)	V _{DD} = 5.0V, V _O = 0.4V, V _I = V _{DD} V _{DD} = 10V, V _O = 0.5V, V _I = V _{DD}	0.35 0.72		0.3 0.6	1.0 2.5		0.24 0.48		mA
i _{DP}	Output Drive Current P-Channel (4002)	V _{DD} = 5.0V, V _O = 2.5V, V _I = V _{SS} V _{DD} = 10V, V _O = 9.5V, V _I = V _{SS}	-0.35 -0.3		-0.3 -0.25	-2.0 -1.0		-0.24 -0.2		mA
I _{DN}	Output Drive Current N-Channel (4012)	V _{DD} = 5.0V, V _O = 0.4V, V _I = V _{DD} V _{DD} = 10V, V _O = 0.5V, V _I = V _{DD}	0.145 0.3		0.12 0.25	0.5 0.6		0.095 0.2		mA
I _{DP}	Output Drive Current P-Channel (4012)	V _{DD} = 5.0V, V _O = 2.5V, V _I = V _{SS} V _{DD} = 10V, V _O = 9.5V, V _I = V _{SS}	-0.145 -0.35		-0.12 -0.3	-0.5 -1.2		-0.095 -0.24		mA
I _I	Input Current					10				pA

AC Electrical Characteristics

$T_A = 25^\circ\text{C}$, $C_L = 15\text{ pF}$, and input rise and fall times = 20 ns.
Typical temperature coefficient for all values of $V_{DD} = 0.3\%/^\circ\text{C}$

Parameter	Conditions	Min.	Typ.	Max.	Units
CD4002M					
t_{PHL} Propagation Delay Time High to Low Level	$V_{DD} = 5.0\text{V}$		35	50	ns
	$V_{DD} = 10\text{V}$		25	40	ns
t_{PLH} Propagation Delay Time Low to High Level	$V_{DD} = 5.0\text{V}$		35	50	ns
	$V_{DD} = 10\text{V}$		25	40	ns
t_{THL} Transition Time High to Low Level	$V_{DD} = 5.0\text{V}$		65	175	ns
	$V_{DD} = 10\text{V}$		35	75	ns
t_{TLH} Transition Time Low to High Level	$V_{DD} = 5.0\text{V}$		65	125	ns
	$V_{DD} = 10\text{V}$		35	70	ns
C_{IN} Input Capacitance	Any Input		5.0		pF
CD4002C					
t_{PHL} Propagation Delay Time High to Low Level	$V_{DD} = 5.0\text{V}$		35	120	ns
	$V_{DD} = 10\text{V}$		25	65	ns
t_{PLH} Propagation Delay Time Low to High Level	$V_{DD} = 5.0\text{V}$		35	80	ns
	$V_{DD} = 10\text{V}$		25	55	ns
t_{THL} Transition Time High to Low Level	$V_{DD} = 5.0\text{V}$		65	300	ns
	$V_{DD} = 10\text{V}$		35	125	ns
t_{TLH} Transition Time Low to High Level	$V_{DD} = 5.0\text{V}$		65	200	ns
	$V_{DD} = 10\text{V}$		35	115	ns
C_{IN} Input Capacitance	Any Input		5.0		pF

AC Electrical Characteristics

$T_A = 25^\circ\text{C}$, $C_L = 15\text{ pF}$, and input rise and fall times = 20 ns.
Typical temperature coefficient for all values of $V_{DD} = 0.3\%/^\circ\text{C}$

Parameter	Conditions	Min.	Typ.	Max.	Units
CD4012M					
t_{PHL} Propagation Delay Time High to Low Level	$V_{DD} = 5.0\text{V}$		50	75	ns
	$V_{DD} = 10\text{V}$		25	40	ns
t_{PLH} Propagation Delay Time Low to High Level	$V_{DD} = 5.0\text{V}$		50	75	ns
	$V_{DD} = 10\text{V}$		25	40	ns
t_{THL} Transition Time High to Low Level	$V_{DD} = 5.0\text{V}$		75	125	ns
	$V_{DD} = 10\text{V}$		50	75	ns
t_{TLH} Transition Time Low to High Level	$V_{DD} = 5.0\text{V}$		75	100	ns
	$V_{DD} = 10\text{V}$		40	60	ns
C_{IN} Input Capacitance	Any Input		5.0		pF
CD4012C					
t_{PHL} Propagation Delay Time High to Low Level	$V_{DD} = 5.0\text{V}$		50	100	ns
	$V_{DD} = 10\text{V}$		25	50	ns
t_{PLH} Propagation Delay Time Low to High Level	$V_{DD} = 5.0\text{V}$		50	100	ns
	$V_{DD} = 10\text{V}$		25	50	ns
t_{THL} Transition Time High to Low Level	$V_{DD} = 5.0\text{V}$		75	150	ns
	$V_{DD} = 10\text{V}$		50	100	ns
t_{TLH} Transition Time Low to High Level	$V_{DD} = 5.0\text{V}$		75	125	ns
	$V_{DD} = 10\text{V}$		40	75	ns
C_{IN} Input Capacitance	Any Input		5.0		pF

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.